

Title (en)  
METHOD FOR PRODUCING AN ARTIFICIAL SAPPHIRE SINGLE CRYSTAL

Title (de)  
VERFAHREN ZUR HERSTELLUNG EINES KÜNSTLICHEN SAPHIR-EINKRISTALLS

Title (fr)  
PROCÉDÉ DE PRODUCTION D'UN MONOCRISTAL DE SAPHIR ARTIFICIEL

Publication  
**EP 4271857 A1 20231108 (DE)**

Application  
**EP 21840775 A 20211228**

Priority  
• AT 511462020 A 20201229  
• AT 2021060490 W 20211228

Abstract (en)  
[origin: WO2022140808A1] The invention relates to a method for producing an artificial sapphire single crystal. Starting with the step of crystal growth, a temperature difference  $\Delta T$ , selected from a range of 1 °C to 60 °C, is set between an Al<sub>2</sub>O<sub>3</sub> melt surface and a boundary surface of the growing sapphire single crystal to the Al<sub>2</sub>O<sub>3</sub> melt, and this temperature difference  $\Delta T$  is kept constant at least over a greater part of the duration of the crystal growth.

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CPC (source: AT EP)  
**C30B 11/003** (2013.01 - EP); **C30B 11/006** (2013.01 - AT EP); **C30B 29/20** (2013.01 - AT EP)

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